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Microstructure and $J_{\rm C}$ Characteristics of Er123 Films With Artificial Pinning Centers

Masashi Mukaida, Tomoya Horide, Yuki Shingai, Ataru Ichinose, Kaname Matsumoto, Shigeru Horii, Ryusuke Kita, Yutaka Yoshida, Satoshi Awaji, Kazuo Watanabe, Ryo Teranishi, Kazuhiro Yamada, and Nobuyuki Mori

Abstract-Critical current density and surface resistance are evaluated for dilute Zn substituted high quality $ErBa_2Cu_3O_{7-\delta}$ films. Dilute Zn substituted ErBa₂Cu₃O₇₋₆ films are grown on SrTiO₃ substrates by a pulsed laser deposition technique. Targets used in the experiments are un-substituted, 0.3at. %, 0.5at.%, 1.0at.% and 10at.% Zn substituted $ErBa_2Cu_3O_{7-\delta}$ ceramics. Crystal structures, field angular dependence of critical current density and surface resistance are evaluated. Zn substituting into $YBa_2Cu_3O_{7-\delta}$ has been studied for understanding the origin of oxide superconductivity with substituting level of several %. In this study, dilute Zn below 1.0 at.% is mainly adopted. Further substitution reduces its critical temperature. We intended to introduce zero-dimensional superconductivity killer atoms into CuO₂ plane as artificial pinning centers. The obtained Zn substituted $ErBa_2Cu_3O_{7-\delta}$ films are *c*-axis oriented without peaks from other phases. The sharp drop temperature of surface resistance decreases as the Zn substitution. However, the surface resistance at a low temperature around 20K is almost the same among the $ErBa_2Cu_3O_{7-\delta}$ films with different Zn substitution. We also measured the field angular dependence of critical current density of the Zn substituted ErBa₂Cu₃O_{7-δ} films. There are no strong angular dependences. Dilute zinc substitution increases critical current density for almost of all directions. However, in a high magnetic field of several tesla, pinning force around the field direction of a-axis is enhanced. Double introduction of one dimensional artificial pinning centers such as BaZrO3 nano-rods and zero dimensional artificial pinning centers is thought to be very effective for increasing critical current density for power cable applications.

Index Terms— $ErBa_2Cu_3O_{7-\delta}$ Zn J_C R_S artificial pinning center.

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M. Mukaida, Y. Shingai, R. Teranishi, K. Yamada, and N. Mori are with Kyushu University, Motooka, Nishi-ku, Fukuoka, Fukuoka 819-0395 Japan (e-mail: mukaida@zaiko.kyushu-u.ac.jp; shingai@zaiko10. zaiko.kyushu-u.ac.jp; teranishi@zaiko.kyushu-u.ac.jp; yamada@zaiko. kyushu-u.ac.jp; mori-ny@zaiko.kyushu-u.ac.jp).

T. Horide and K. Matsumoto are with Kyoto University, Yoshidahonmachi, Sakyo-ku, Kyoto, Kyoto 606-8501 Japan (e-mail: tomoya.horide@t04.mbox.media.kyotou. ac.jp; kaname.matsumoto@materials.mbox.media.kyoto-u.ac.jp).

A. Ichinose is with the Central Research Institute of Electric Power Industry, Yokosuka, Kanagawa, 240-0196 Japan (e-mail: ai@criepi.denken.or.jp).

S. Horii is with the University of Tokyo, Hongo, Bunkyo-ku, Tokyo 113-8656 Japan (e-mail: tholy@mail.ecc.u-tokyo.ac.jp).

R. Kita is with Shizuoka University, Johoku, Hamamatsu, Shizuoka 430-850 Japan (e-mail: terkita@ipc.shizuoka.ac.jp).

Y. Yoshida is with Nagoya University, Furocho, Chikusa-ku, Nagoya, Aichi 464-8603 Japan (e-mail: yoshida@nuee.nagoya-u.ac.jp).

S. Awaji and K. Watanabe are with Tohoku University, Katahira, Aoba-ku, Sendai, Miyagi 980-8577 Japan (e-mail: awaji@imr.tohoku.ac.jp; kwata@imr.tohoku.ac.jp).

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I. INTRODUCTION

 \frown INCE the discovery of high $T_{\rm C}$ superconductors (HTSs) with a critical temperature as high as a liquid nitrogen temperature, significant effort has been directed toward fabricating superconducting films with high critical current density $(J_{\rm C})$. Superconducting cables as developed by Sumitomo Electric Industries [1] by using Bi2223 materials, have a high $T_{\rm C}$ and high $J_{\rm C}$. However, HTSs have anisotropic crystal structures as well as transport properties. [2]-[4] Bi family superconducting cables can not fed high superconducting current in a magnetic field around 77.3 K. Critical current density of REBa₂Cu₃O_{7- δ} (RE: Lanthanoide or Y atoms) high T_C superconducting films at 77.3 K is also relatively lower than that of low $T_{\rm C}$ metal superconductors at 4.2 K in magnetic fields. In order to apply high $T_{\rm C}$ superconductors for power applications, $J_{\rm C}$ s in magnetic fields must be as high as those of metal superconductors at 4.2 K.

Recently, many papers have appeared for the introduction of artificial pinning centers. [5]-[15] These artificial pinning centers are categorized into 4 groups. One is 0-dimensional artificial pinning centers which are atomic substitution of RE [16], Ba or Cu [5]-[8], [17] atoms. Dilute (minute) doping is essential for this type of artificial pinning centers. Next is 1-dimensional artificial pinning centers which are columnar defects induced by nano-particles [9], mosaic surface [18], [19] or heavy ion implantation [20]-[22]. The second is 2-dimensional artificial pinning centers which are grain boundary or thin precipitates. [10], [23] Above 2 artificial pinning centers (1-D and 2-D) have a magnetic field angular dependence. Then, it is effective to improve $J_{\rm C} - B$ characteristics by introducing *c*-axis correlated artificial pinning centers. The last is the 3-dimensional artificial pinning centers which are insulating nano-particles [24] and nano-low $T_{\rm C}$ particles [13], [25], mixed RE atoms [26] and nano-noble metals such as Au.

In this paper, we report relations between the field angular dependencies and their microstructures of $ErBa_2Cu_3O_{7-\delta}$ films with 0-dimensional artificial pinning centers.

II. EXPERIMENTS

Zn substituted ErBa₂Cu₃O_{7- δ} films were grown by pulsed ArF excimer laser (Lambda Physik) deposition. The background pressure of the growth chamber (ULVAC) was 4×10^{-8} Pa. The targets used in this experiment was sintered Zn substituted ErBa₂Cu_{3(1-x)}Zn_{3x}O_{7- δ} ceramics. The incident laser beam was focused on the target surface at 45° through an MgF₂ window. The focusing lens was also made of MgF₂ to avoid laser power absorption. The laser irradiated area was about 2 mm². The laser power was between 200 ~ 300 mJ/pulse. The energy density measured on the target was about $6 \sim 9 \text{ J/cm}^2$ through the window and the lens. The pulse frequency was fixed at 1 Hz. SrTiO₃ (100) substrates were used in this experiment. The substrate was attached by silver paste to a rotating metal substrate holder, which was irradiated by a lamp heater. The substrate temperature was controlled by input power monitored by a thermocouple and calibrated by an optical pyrometer. The substrate temperature was determined using an optical pyrometer. In this experiment, the substrate temperature was fixed near 750 °C.

During deposition, the oxygen pressure was fixed at 53.3 Pa with an oxygen flow rate of 200 cc/min. After deposition, the substrate was cooled to a room temperature without any annealing processes. It is reported that additional annealing processes increase the $J_{\rm C}$ of ErBa₂Cu₃O_{7- δ} films. [27] However, in order to clarify the $J_{\rm C}$ enhancement by the introduction of pinning centers, we do not anneal the films.

The preferred orientations of $ErBa_2Cu_3O_{7-\delta}$ films with artificial pinning centers were determined by measuring the $\theta/2\theta$ scan of the films by x-ray diffraction (XRD) with $Cu - K_{\alpha}$ radiation. The in-plane orientations of the $ErBa_2Cu_3O_{7-\delta}$ films were evaluated by x-ray ϕ scan (in-plane rotation) using the (102) plane of $ErBa_2Cu_3O_{7-\delta}$. The film crystallinity was estimated by full width at the half maximum (FWHM) of the rocking curve using 005 peak of the $ErBa_2Cu_3O_{7-\delta}$ film.

The film thickness is measured by a scanning electron microscope (JSM-6500F) and a mechanical stylus. The lattice images of the films were observed by a transmission electron microscope (TEM).

Critical currents are measured by a conventional four-probe method in a magnetic field. Samples with a 100 μ m width are fabricated by a photolithography and a wet etching method. The criterion 1 μ V/cm is used to define the critical current. The samples were rotated maintaining $J \perp H$ (maximum Lorentz force). The angle θ between H and the normal to the films which coincides with the crystallographic *c*-axis within 0.5 degrees.

III. RESULT AND DISCUSSIONS

Fig. 1 shows a typical x-ray diffraction (XRD) pattern of the as-grown Zn substituted $ErBa_2Cu_3O_{7-\delta}$ films with Zn concentration of 10 at%. The obtained $ErBa_2Cu_3O_{7-\delta}$ films with artificial pinning centers have *c*-axis preferred orientation. The figure is almost the same as that of the non-doped $ErBa_2Cu_3O_{7-\delta}$ films. Then, it is concluded that Zn in 10 at% Zn substituted $ErBa_2Cu_3O_{7-\delta}$ films is not substituted or Zn is substituted with remaining the 123 crystal structure. The reduced Zn concentration $ErBa_2Cu_3O_{7-\delta}$ films from 1 at% to 0.3 at% also showed the same XRD patterns.

Then we measured surface resistance of the films. Fig. 2 shows surface resistance of $ErBa_2Cu_3O_{7-\delta}$ films with varied Zn substitution. The surface resistance of the 10 % Zn substituted $ErBa_2Cu_3O_{7-\delta}$ films showed low T_C which is nearly coincide with the bulk T_C with 10 % Zn substitution. By reducing the Zn substitution, T_C of the $ErBa_2Cu_3O_{7-\delta}$ films goes up. The optimum substitution level of Zn for Cu in



Fig. 1. A typical x-ray diffraction pattern for Zn substituted $ErBa_2Cu_3O_{7-\delta}$ films on $SrTiO_3$ substrates.



Fig. 2. Surface resistance of $ErBa_2Cu_3O_{7-\delta}$ films with varied Zn substitution for Cu. T_C depend on the amount of the Zn substitution. However, at a low temperature around 20 K, the surface resistance is independent of the Zn substitution.

ErBa₂Cu₃O_{7- δ} films may be below 0.3 at%. We used 3N (99.9 %) raw materials to prepare targets. Then, the limitation of doping level is 0.1 at% from the impurity level of raw materials. To get thinner doped films we must use higher purity raw materials. The highest $T_{\rm C}$ is obtained in non (Zn = 0%) substitution ErBa₂Cu₃O_{7- δ} films. However, the surface resistance at a low temperature is the highest for the non (Zn = 0%)substitution ErBa₂Cu₃O_{7- δ} films. It means that the Zn substitution is effective for the reduction of surface resistance however, substitution in the CuO₂ plane is too strong. May be another 0-dimentional pinning centers such as RE materials which substitute for Y, or Alkaline earth element Sr for Ba are also available. The most interesting phenomenon is that the surface resistance at a low $T_{\rm C}$ around 20 K is almost the same for all Zn substituted ErBa₂Cu₃O_{7- δ} films.

Next we measured the field angular dependence of $J_{\rm C}$. Fig. 3 shows the field angular dependence of $J_{\rm C}$ measured at 77.3 K.



Fig. 3. Field angular dependence of 0.3 at% Zn substituted $\rm ErBa_2Cu_3O_{7-\delta}$ films.

Angle θ is the angle between *c*-axis of the ErBa₂Cu₃O_{7- δ} film and the magnetic field. Then the direction of 90° is that of the *a*-axis.

In a low magnetic field, $J_{\rm C}$ is low at around 70°. $J_{\rm C}$ in the magnetic field along the *a*-axis is the highest. $J_{\rm C}$ in the magnetic field along the *c*-axis is not the lowest. Then there are some *c*-axis correlated pinning centers. However, no strong anisotropic field angular dependences are observed comparing to the films with 1-dimensional artificial pinning centers [12].

We introduced Zn as 0-dimensional artificial pinning centers which have no angular dependence of the field direction. However, $J_{\rm C}$ of the Zn substituted ${\rm ErBa}_2{\rm Cu}_3{\rm O}_{7-\delta}$ film did not increase uniformly for every magnetic direction.

On the contrary, the 0.3 at% Zn substituted $ErBa_2Cu_3O_{7-\delta}$ film showed a *a*-axis correlated pinning force in a high magnetic field. Around the 90° (75-105°), no reductions of J_C against the magnetic field up to 6 T were observed. Non dope $ErBa_2Cu_3O_{7-\delta}$ films have greater dependence of the magnetic field along the *a*-axis. There may be some defects induced by the Zn addition to the $ErBa_2Cu_3O_{7-\delta}$ films. Then we observed cross-sectional TEM images of the 1 at% Zn substituted $ErBa_2Cu_3O_{7-\delta}$ films to clarify the effect of Zn substitution on the microstructure of $ErBa_2Cu_3O_{7-\delta}$ films.

Fig. 4 shows a low magnified cross-sectional TEM image of the 1 at% Zn substituted $ErBa_2Cu_3O_{7-\delta}$ film. From the image, the total thickness of the film is around 500nm. There are no big defects or columnar defects as shown in Fig. 4. However, there are many dark spots in the films. Then, we focus on the dark spots. Fig. 5 shows the high resolution TEM image around the dark spots in the 1 at% Zn substituted $ErBa_2Cu_3O_{7-\delta}$ film. Around the dark spots, we can find many stacking faults in the Zn substituted $ErBa_2Cu_3O_{7-\delta}$ film. Every stacking fault runs along the *a*-axis. Very strong pinning force as shown in Fig. 3 is thought to be due to the stacking faults. Then it is concluded that doped Zn in to the $ErBa_2Cu_3O_{7-\delta}$ film was not uniformly distributed in to CuO_2 plane. Furthermore Zn substitution for Cu in CuO_2 plane is too strong. Even a small amount of Zn can



Fig. 4. A low magnified TEM image of the 1 at% Zn substituted ${\rm ErBa_2Cu_3O_{7-\delta}}$ film.



Fig. 5. A high resolution TEM image around the dark spots in the 1 at% Zn substituted $ErBa_2Cu_3O_{7-\delta}$ film as shown in Fig. 4.

destroy superconductivity. It is difficult to enhance J_{CS} by substituting Cu atoms in CuO₂ plane with another atoms. Another 0- dimensional artificial pinning centers which substitute for Ba or RE are strictly required.

IV. CONCLUSION

We have evaluated the critical current density and surface resistance of dilute Zn substituted $ErBa_2Cu_3O_{7-\delta}$ films. Dilute Zn substituted $ErBa_2Cu_3O_{7-\delta}$ films were grown on $SrTiO_3$ substrates by a pulsed laser deposition technique. The obtained Zn substituted $ErBa_2Cu_3O_{7-\delta}$ films were *c*-axis oriented with high crystalline quality from the XRD measurements. Zn below 1.0at. % substitution is mainly adopted because, the further substitution reduces its *T*.

The sharp drop temperature of surface resistance decreases as the Zn substitution. However, the surface resistance at a low temperature around 20 K is almost the same for the $ErBa_2Cu_3O_{7-\delta}$ films with different Zn substitution. We also measured the field angular dependence of critical current density of the Zn substituted $ErBa_2Cu_3O_{7-\delta}$ films. There are no strong angular dependences comparing to the films with 1-dimensional artificial pinning centers. Dilute zinc substitution increases critical current density for almost of all directions. However, in a high magnetic field of several tesla, pinning force around the field direction of *a*-axis was enhanced. The $J_{\rm C}$ enhancement along the *a*-axis is due to the stacking faults as observed in the cross-sectional TEM images.

Even a small amount of Zn can destroy superconductivity, then, it is difficult to enhance $J_{\rm C}$ s greatly by substituting Cu atoms in CuO₂ plane with another atoms. Another 0- dimensional artificial pinning centers which substitute for Ba or RE sites are strictly required.

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